



High Speed SRAM

32K-Word By 8 Bit

CS18HS02565

Revision History

<u>Rev. No.</u>	<u>History</u>	<u>Issue Date</u>	<u>Remark</u>
1.3	Add green code in part no.	Jul. 22, 2005	
1.4	Add in 28L TSOP 1-8x13.4mm	Mar. 10,2006	
1.5	Remove 28L TSOP 1-8x13.4mm	Jun. 12,2006	
1.6	Revise speed option and DC/AC Characteristics.	Mar. 05,2007	
1.7	Remove 28L PDIP 300mil	Apr. 24,2007	
1.8	Increase version description in Order Information	Sep, 05, 2008	



High Speed SRAM

32K-Word By 8 Bit

CS18HS02565

■ DESCRIPTION

The CS18HS02565 series products are 32,768-words by 8-bits static RAMs fabricated with advanced 8" wafer submicron CMOS technology. Using unique CMOS peripheral circuits and special poly-load 4-transistor memory cells, the CS18HS02565 series products exhibit very high-speed performance with single +5-volt power supply while requiring low power and no clock or refreshing to operate. The CS18HS02565 is packed in 28-pin SOP-330mil and 28-pin SOJ-300mil.

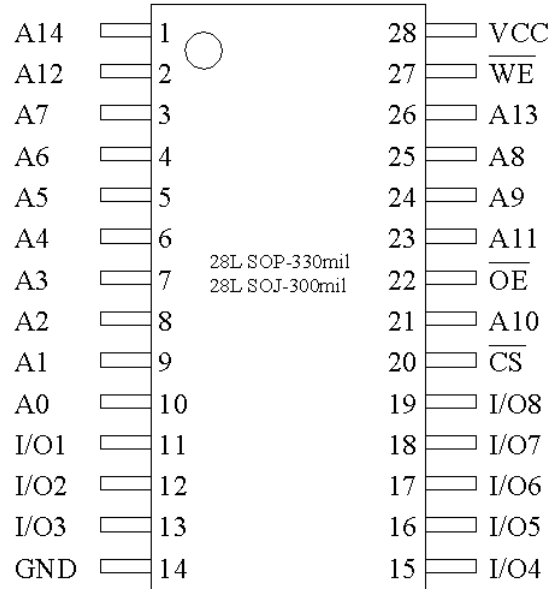
■ FEATURES

1. 32,768-word x 8-bit organization
2. Operation voltage: 4.5 ~ 5.5V
3. Fully static operation: no clock or refreshing required
4. LVTTTL-compatible inputs and outputs
5. Common I/O capability
6. Low power consumption
 - Active: 45/35 mA (Max.)
 - Standby: 350 μ A
7. Very high speed access: 10/12 ns
8. Output Enable (\overline{OE}) available for very fast access

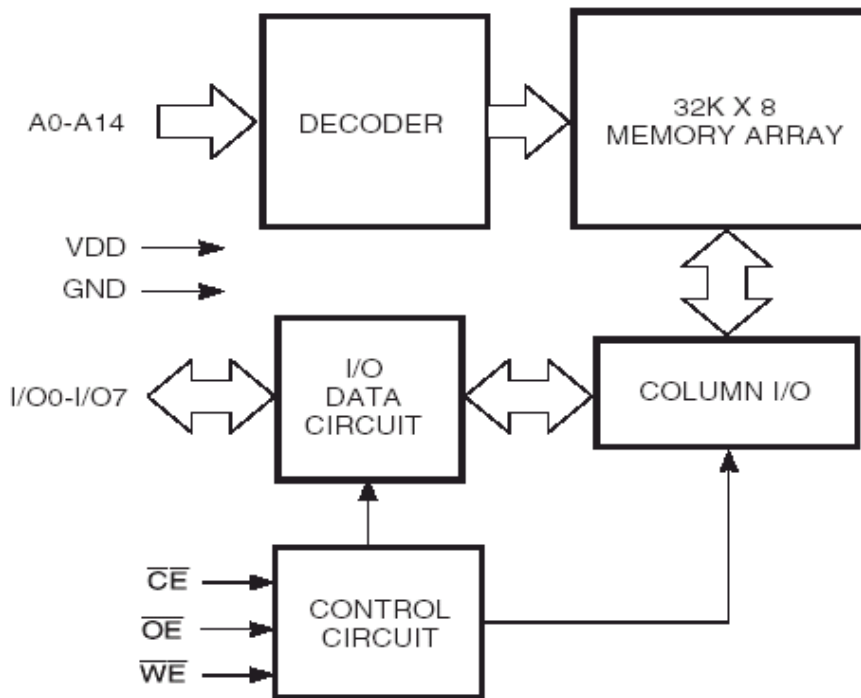
■ Product Family

Part No.	Operating Temp	Vcc. Range	Speed (ns)	Supply Current mA (Max.)	Package Type
CS18HS02565	0~70°C	4.5~5.5V	10	45	28 SOP-330mil 28 SOJ-300mil
			12	35	

■ PIN CONFIGURATIONS



■ BLOCK DIAGRAM





High Speed SRAM

32K-Word By 8 Bit

CS18HS02565

■ PIN DESCRIPTIONS

Symbols	Functions
A0~A14	Address Inputs
I/O1~I/O8	Data Inputs / Outputs
\overline{CS}	Chip Select Input
\overline{WE}	Write Enable Input
\overline{OE}	Output Enable Input
V _{CC}	Power Supply
V _{SS}	Ground

■ TRUTH TABLE

\overline{CS}	\overline{OE}	\overline{WE}	Mode	I/O1~I/O8	V _{CC} Current
H	X	X	Not Selected	High Z	ISB, ISB1
L	H	H	Output Disable	High Z	IDD
L	L	H	Read	Data Out	IDD
L	X	L	Write	Data In	IDD

■ ABSOLUTE MAXIMUM RATINGS

Parameters	Rating	Unit
Supply Voltage to V _{SS}	-0.5 to +7.0	V
Input/Output to V _{SS}	-0.5 to V _{CC} +0.5	V
Allowable Power Dissipation	1.5	W
Storage Temperature	-65 to +150	°C
Operating Temperature	0 to +70	°C

■ OPERATING RANGE

Range	Ambient Temperature	V _{CC}
Commercial	0~70°C	5.0V±5%



High Speed SRAM

32K-Word By 8 Bit

CS18HS02565

■ DC ELECTRICAL CHARACTERISTICS

($V_{CC} = 5V$, $V_{SS} = 0V$, $T_a = 0$ to $70^{\circ}C$)

Parameters	Symbols	Test Conditions	Min.	Typ.	Max	Unit	
Input Low Voltage	V_{IL}	-	-0.3	-	0.8	V	
Input High Voltage	V_{IH}	-	2.2	-	$V_{CC}+0.5$	V	
Input Leakage Current	I_{LI}	$V_{IN} = V_{SS}$ to V_{CC}	-1	-	+1	μA	
Output Leakage Current	I_{LO}	$V_{I/O} = V_{SS}$ to V_{CC} , $\overline{CS} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$	-1	-	+1	μA	
Output Low Voltage	V_{OL}	$I_{OL} = +8.0mA$	-	-	0.4	V	
Output High Voltage	V_{OH}	$I_{OH} = -4.0mA$	2.4	-	-	V	
Operating Power Supply Current	I_{DD}	$\overline{CS} = V_{IL}$, $I/O = 0$ mA Cycle = MIN Duty = 100%	10	-	-	45	mA
			12	-	-	35	mA
Standby Power Supply Current	I_{SB}	$\overline{CS} = V_{IH}$, Cycle = MIN Duty = 100%	-	-	1	mA	
	I_{SB1}	$\overline{CS} \geq V_{CC} - 0.2V$	-	-	350	μA	

Note: Typical characteristics are measured at $V_{CC} = 5V$, $T_a = 25^{\circ}C$

■ AC Characteristics: Capacitances

($V_{CC} = 5V$, $T_a = 25^{\circ}C$, $f = 1$ MHz)

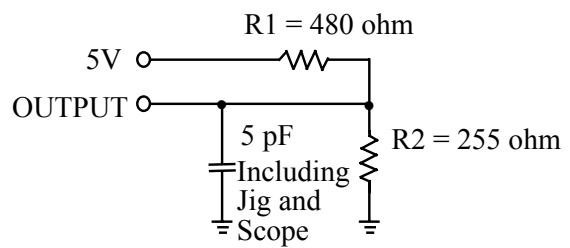
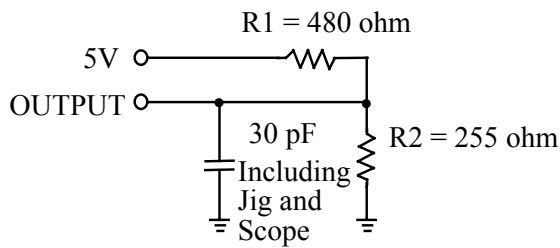
Parameters	Symbols	Conditions	Max.	Unit
Input Capacitance	C_{IN}	$V_{IN} = 0V$	8	pF
Input/Output Capacitance	$C_{I/O}$	$V_{OUT} = 0V$	10	pF

Note: These parameters are sampled but not 100% tested.

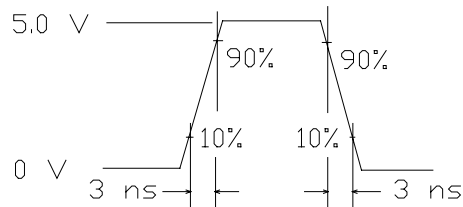
AC Test Conditions

Parameters	Conditions
Input Pulse Levels	0V to 3V
Input Rise and Fall Times	3 ns
Input and Output Timing Reference Level	1.5V
Output Load	CL = 30 pF, IOH/IOL = -4 mA / 8 mA

■ AC Test Loads and Waveforms



(For T_{CLZ}, T_{OLZ}, T_{CHZ}, T_{OHZ}, T_{WHZ}, T_{OW})





High Speed SRAM

32K-Word By 8 Bit

CS18HS02565

■ AC Performances:

(V_{CC} = 5V, V_{SS} = 0V, T_a = 0 to 70°C)

(1) Read Cycle

Parameters	Symbols	CS18HS02565-10		CS18HS02565-12		Unit
		Min.	Max.	Min.	Max.	
Read Cycle Time	TRC	10	-	12	-	ns
Address Access Time	TAA	-	10	-	12	ns
Chip Select Access Time	TACS	-	10	-	12	ns
Output Enable to Output Valid	TAOE	-	6	-	6	ns
Chip Selection to Output in Low Z	TCLZ*	2	-	3	-	ns
Output Enable to Output in Low Z	TOLZ*	0	-	0	-	ns
Chip Deselection to Output in High Z	TCHZ*	-	5	-	6	ns
Output Disable to Output in High Z	TOHZ*	-	5	-	7	ns
Output Hold from Address Change	TOH	2	-	2	-	ns

■ These parameters are sampled but not 100% tested

(2) Write Cycle

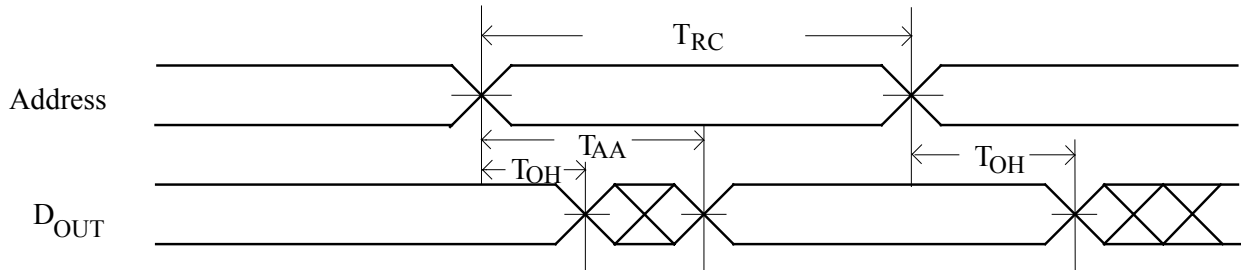
Parameters	Symbols	CS18HS02565-10		CS18HS02565-12		Unit
		Min.	Max.	Min.	Max.	
Write Cycle Time	TWC	10	-	12	-	ns
Chip Selection to End of Write	TCW	9	-	10	-	ns
Address Valid to End of Write	TAW	9	-	10	-	ns
Address Setup Time	TAS	0	-	0	-	ns
Write Pulse Width	TWP	9	-	9	-	ns
Write Recovery Time	TWR	0	-	0	-	ns
Data Valid to End of Write	TDW	7	-	7	-	ns
Data Hold from End of Write	TDH	0	-	0	-	ns
Write to Output in High Z	TWHZ*	-	6	-	6	ns
Output Disable to Output in High Z	TOHZ*	-	6	-	6	ns
Output Active from End of Write	TOW	0	-	0	-	ns

■ These parameters are sampled but not 100% tested

■ Timing Waveforms

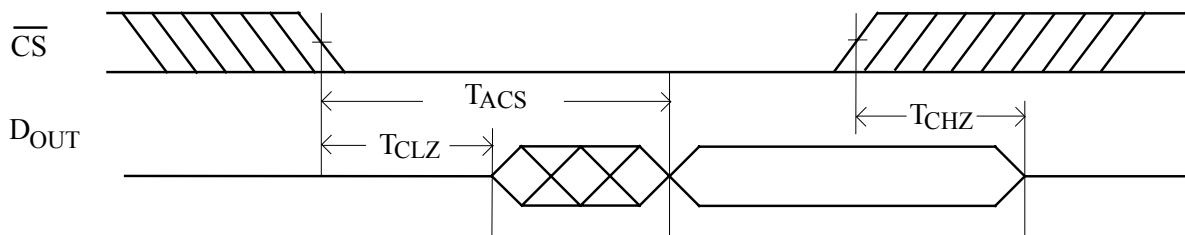
Read Cycle 1

(Address Controlled)



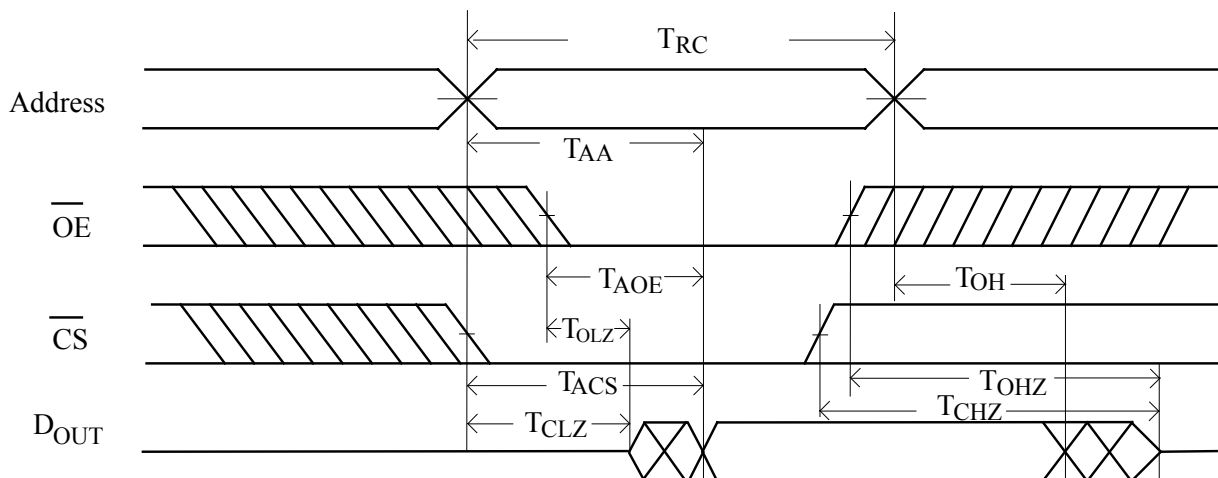
Read Cycle 2

(Chip Select Controlled)



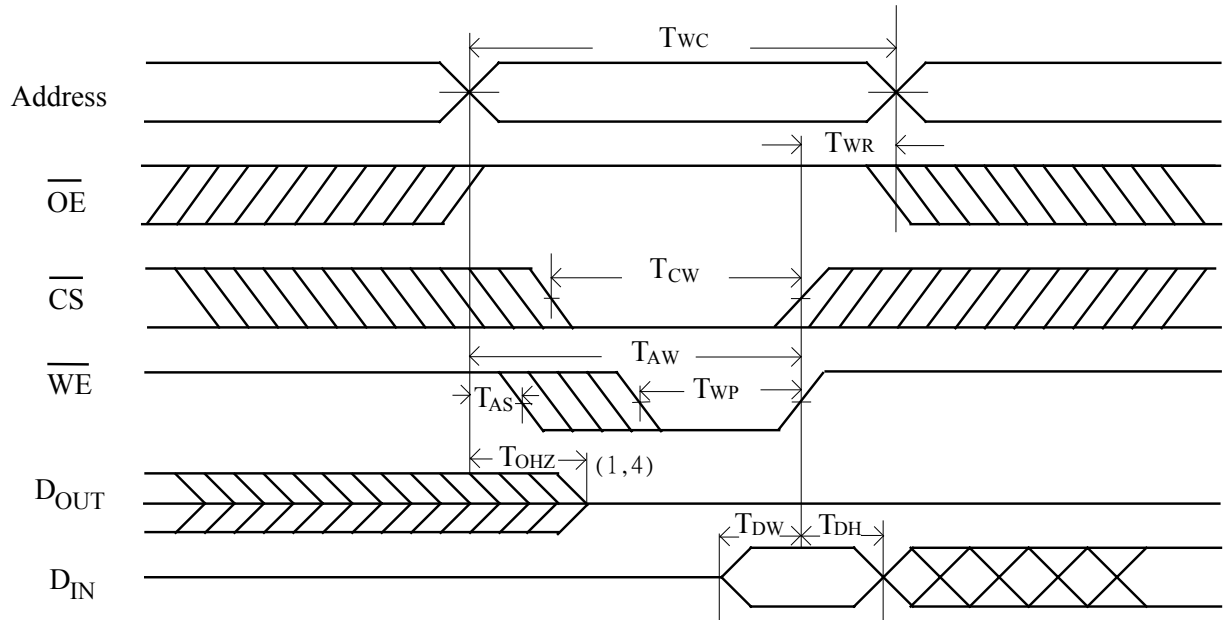
Read Cycle 3

(Output Enable Controlled)



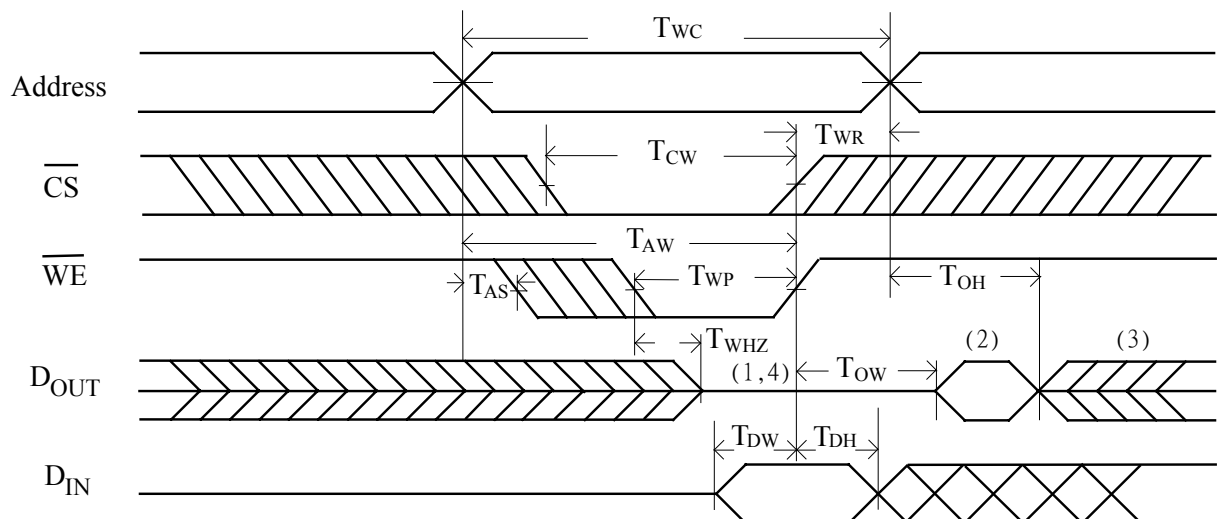
Write Cycle 1

(\overline{OE} Clock)



Write Cycle 2

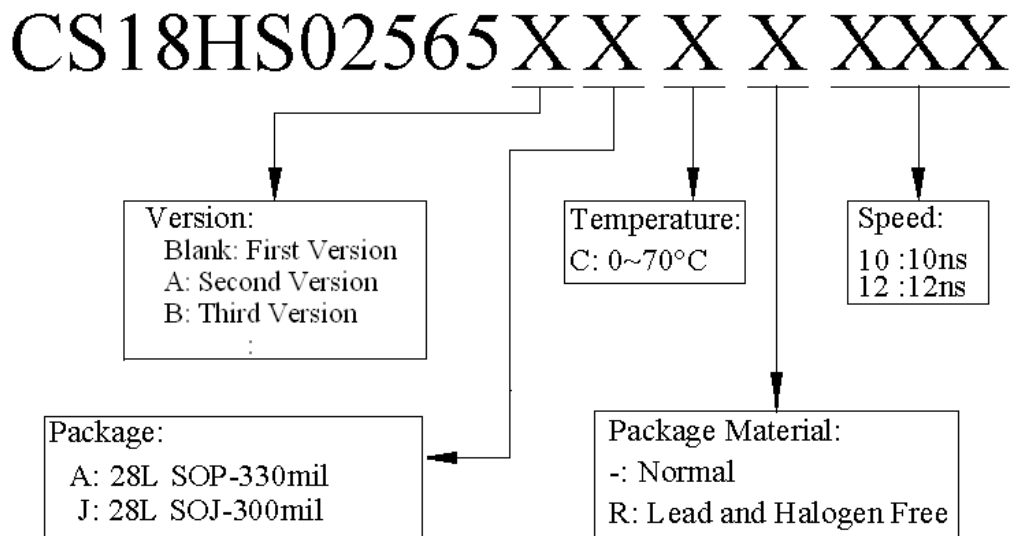
($\overline{OE} = V_{IL}$ Fixed)



Notes:

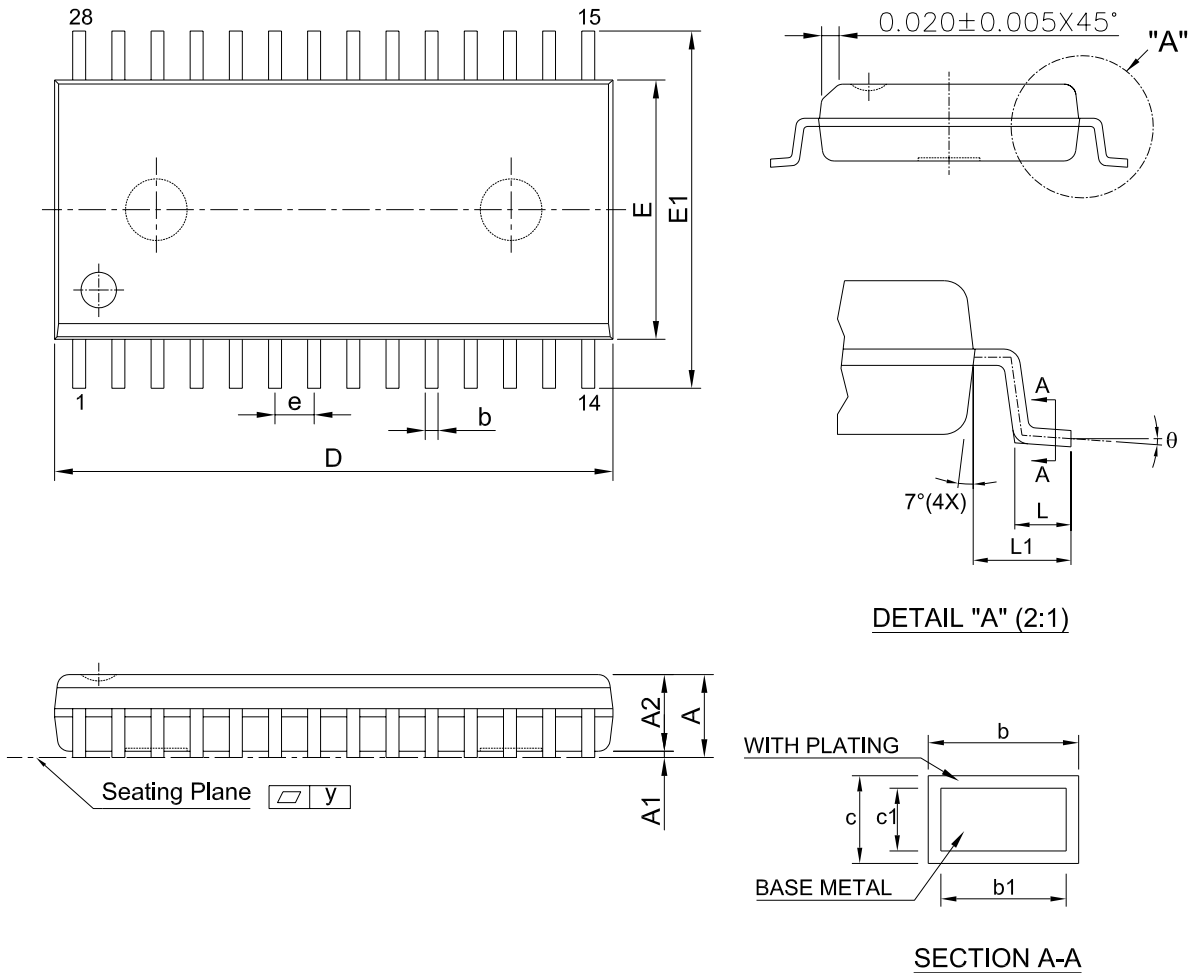
1. During this period, I/O pins are in the output state, so input signals of opposite phase to the outputs should not be applied.
2. The data output from D_{OUT} are the same as the data written to D_{IN} during the write cycle.
3. D_{OUT} provides the read data for the next address.
4. Transition is measured $\pm 500\text{mV}$ from steady state with $C_L = 5\text{pF}$. This parameter is guaranteed but not 100% tested.

■ ORDER INFORMATION



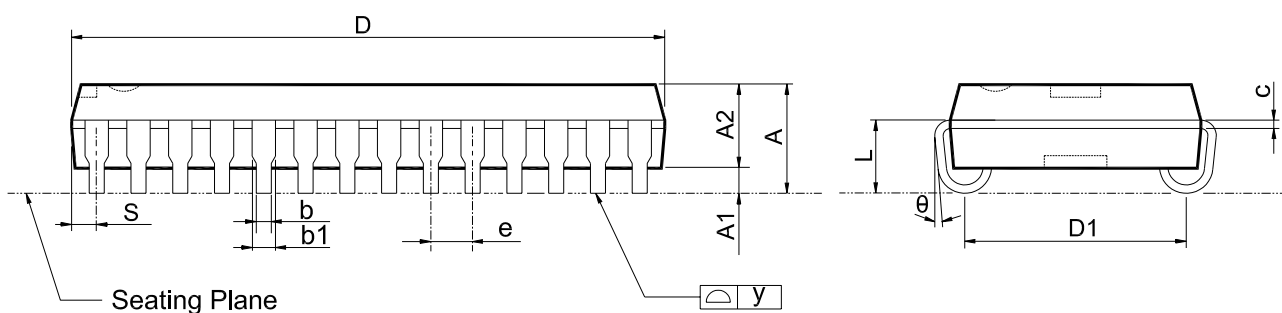
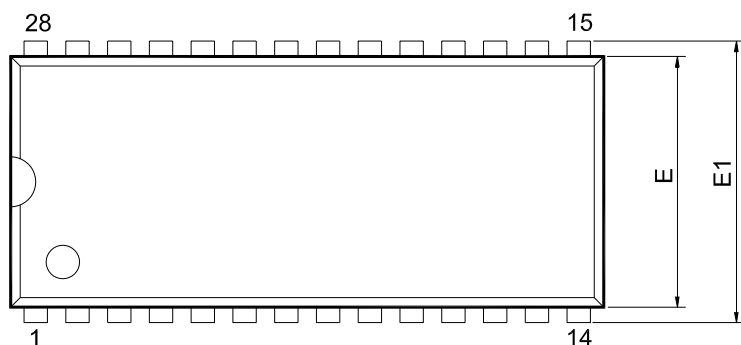
Note: Package material code “R” meets ROHS

■ PACKAGE DIMENSIONS - 28L SOP -330mil



SYMBOL UNIT	A	A1	A2	b	b1	c	c1	D	E	E1	e	L	L1	y	Θ	
	mm	Min.	2.540	0.102	2.362	0.35	0.35	0.20	0.20	17.983	8.280	11.506	1.118	0.700	1.520	-
Nom.		2.692	0.226	2.489	-	-	-	-	18.110	8.407	11.811	1.270	0.964	1.720	-	-
Max.		2.844	0.350	2.616	0.50	0.45	0.32	0.28	18.237	8.534	12.116	1.422	1.228	1.920	0.1	10°
inch	Min.	0.100	0.004	0.093	0.014	0.014	0.008	0.008	0.708	0.326	0.453	0.044	0.0276	0.0598	-	0°
	Nom.	0.106	0.009	0.098	-	-	-	-	0.713	0.331	0.465	0.050	0.0380	0.0677	-	-
	Max.	0.112	0.014	0.103	0.020	0.018	0.012	0.011	0.718	0.336	0.477	0.056	0.0484	0.0756	0.004	10°

■ PACKAGE DIMENSIONS - 28L SOJ -300mil



SYMBOL UNIT	A	A1	A2	b1	b	c	D	E	e	D1	E1	L	S	y	⊖
	mm	Min. —	0.69	2.41	0.66	0.41	0.20	—	7.49	1.12	6.22	8.31	1.96	—	—
	Nom. —	—	2.54	0.71	0.46	0.25	18.03	7.62	1.27	6.73	8.56	2.21	—	—	—
	Max. 3.56	—	2.67	0.81	0.56	0.36	18.54	7.75	1.42	7.24	8.81	2.46	1.14	0.10	10°
inch	Min. —	0.027	0.095	0.026	0.016	0.008	—	0.295	0.044	0.245	0.327	0.077	—	—	0°
	Nom. —	—	0.100	0.028	0.018	0.010	0.710	0.300	0.050	0.265	0.337	0.087	—	—	—
	Max. 0.140	—	0.105	0.032	0.022	0.014	0.730	0.305	0.056	0.285	0.347	0.097	0.045	0.004	10°